REMARKS

The Applicants thank the Examiner for the careful examination of this application and respectfully request the entry of the amendments indicated hereinabove. The Applicants also thank the Examiner for the indication of allowance of Claims 13-19.

Claims 1-29 are pending. Within the pending claim set, Claims 1, 8, 20, 24, and 29 are rejected and Claims 2-7, 9-12, 21-23, and 25-28 are objected to. Claims 1, 3, 9-10, 20, 22, and 26-28 are amended, and Claims 2, 21, and 29 are cancelled hereinabove.

Amended independent Claim 1 positively recites that the second portion of the silicide layer contacts the gate. These advantageously claimed features are not taught or suggested by the patent granted to Grover et al.

Grover et al. teaches away from the advantageously claimed invention because Grover et al. teaches that the silicide layer (33a) does not contact the gate (11s). See Grover et al. FIG. 1 and paragraph 0037.

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The Applicants respectfully traverse the statement that 15s is a barrier region. The Applicants submit that element 15s in Grover et al. is half (i.e. the ptype silicon) of a p-n junction that is in parallel with (but not part of) the Schottky (i.e. element 15s is part of a diode guard ring). The Applicants also respectfully traverse the statement that Grover et al. discusses the metal TiN in paragraph 0066.

Due to the foregoing reasons, the Applicants respectfully traverse the rejection of Claim 1 and respectfully assert that Claim 1 is patentable over Grover et al. Furthermore, Claims 3-12 are allowable for depending on allowable independent Claim 1 and, in combination, including limitations not taught or described in the reference of record.

Amended independent Claim 20 positively recites that the second portion of the silicide layer contacts the gate. These advantageously claimed features are not taught or suggested by the patent granted to Grover et al.

Grover et al. teaches away from the advantageously claimed invention because Grover et al. teaches that the silicide layer (33a) does not contact the gate (11s). See Grover et al. FIG. 1 and paragraph 0037.

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Due to the foregoing reasons, the Applicants respectfully traverse the rejection of Claim 20 and respectfully assert that Claim 20 is patentable over Grover et al. Furthermore, Claims 22-28 are allowable for depending on allowable independent Claim 20 and, in combination, including limitations not taught or described in the reference of record.

For the reasons stated above, this application is believed to be in condition for allowance. Reexamination and reconsideration is requested.

Respectfully submitted,

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